MCR716, MCR718

Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed for high volume, low cost, industrial and consumer applications such as motor control, process control, temperature, light and speed control.

- Small Size
- Passivated Die for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Surface Mount Lead Form — Case 369A
- Device Marking: Device Type, e.g., MCR716, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

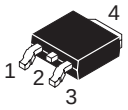
Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage(1) (T_J = –40 to +110°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR716 MCR718	V_{DRM}, V_{RRM}	 400 600	Volts
On–State RMS Current (180° Conduction Angles; T_C = 90°C)	$I_{T(RMS)}$	4.0	Amps
Average On–State Current (180° Conduction Angles; T_C = 90°C)	$I_{T(AV)}$	2.6	Amps
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T_J = 110°C)	I_{TSM}	25	Amps
Circuit Fusing Consideration (t = 8.3 msec)	I^2t	2.6	A^2sec
Forward Peak Gate Power (Pulse Width ≤ 10 μs, T_C = 90°C)	P_{GM}	0.5	Watt
Forward Average Gate Power (t = 8.3 msec, T_C = 90°C)	$P_{G(AV)}$	0.1	Watt
Forward Peak Gate Current (Pulse Width ≤ 10 μs, T_C = 90°C)	I_{GM}	0.2	Amp
Operating Junction Temperature Range	T_J	–40 to +110	°C
Storage Temperature Range	T_{stg}	–40 to +150	°C

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

ON Semiconductor

http://onsemi.com

SCRs
4.0 AMPERES RMS
400 thru 600 VOLTS



D–PAK
CASE 369A
STYLE 4

PIN ASSIGNMENT	
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

Device	Package	Shipping
MCR716T4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)
MCR718T4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	°C/W
Thermal Resistance, Junction to Ambient (Case 369A)(1)	$R_{\theta JA}$	80	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

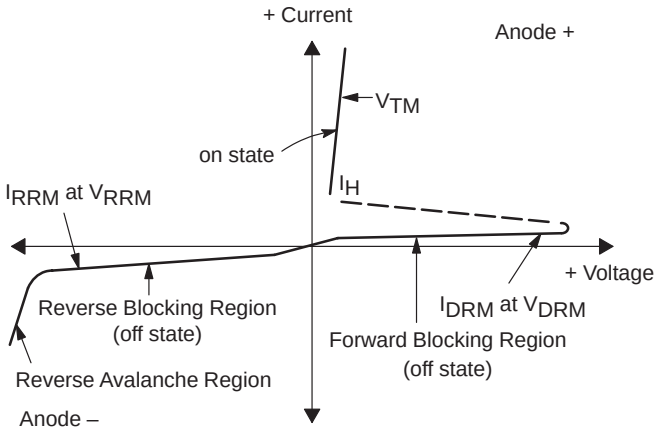
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Forward or Reverse Blocking Current; R_{GK} = 1 KΩ(2)	I_{DRM}				μA
(V_{AK} = Rated V_{DRM} or V_{RRM}) T_C = 25°C	I_{RRM}	—	—	10	
T_C = 110°C		—	—	200	
ON CHARACTERISTICS					
Peak Reverse Gate Blocking Voltage (I_{GR} = 10 μA)	V_{RGM}	10	12.5	18	Volts
Peak Reverse Gate Blocking Current (V_{GR} = 10 V)	I_{RGM}	—	—	1.2	μA
Peak Forward On–State Voltage(3)	V_{TM}				Volts
(I_{TM} = 5.0 A Peak)		—	1.3	1.5	
(I_{TM} = 8.2 A Peak)		—	1.5	2.2	
Gate Trigger Current (Continuous dc)(4)	I_{GT}				μA
(V_D = 12 Vdc, R_L = 30 Ohms) T_C = 25°C		1.0	25	75	
T_C = –40°C		—	—	300	
Gate Trigger Voltage (Continuous dc)(4)	V_{GT}				Volts
(V_D = 12 Vdc, R_L = 30 Ohms) T_C = 25°C		0.3	0.55	0.8	
T_C = –40°C		—	—	1.0	
T_C = 110°C		0.2	—	—	
Holding Current(2)	I_H				mA
(V_D = 12 Vdc, Initiating Current = 200 mA, Gate Open) T_C = 25°C		0.4	1.0	5.0	
T_C = –40°C		—	—	10	
Latching Current(2)	I_L				mA
(V_D = 12 Vdc, I_G = 2.0 mA, T_C = 25°C)		—	—	5.0	
(V_D = 12 Vdc, I_G = 2.0 mA, T_C = –40°C)		—	—	10	
Total Turn-On Time	t_{gt}	—	2.0	5.0	μs
(Source Voltage = 12 V, R_S = 6 KΩ, I_T = 8 A(pk), R_{GK} = 1 KΩ)					
(V_D = Rated V_{DRM}, Rise Time = 20 ns, Pulse Width = 10 μs)					
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off–State Voltage	dv/dt	5.0	10	—	V/μs
(V_D = 0.67 x Rated V_{DRM}, R_{GK} = 1 KΩ, Exponential Waveform, T_J = 110°C)					
Repetitive Critical Rate of Rise of On–State Current	di/dt	—	—	100	A/μs
(f = 60 Hz, I_{PK} = 30 A, PW = 100 μs, dIG/dt = 1 A/μs)					

(1) Case 369A, when surface mounted on minimum recommended pad size.
(2) Ratings apply for negative gate voltage or R_{GK} = 1 KΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.
(3) Pulse Test: Pulse Width ≤ 2 ms, Duty Cycle ≤ 2%.
(4) R_{GK} current not included in measurements.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current



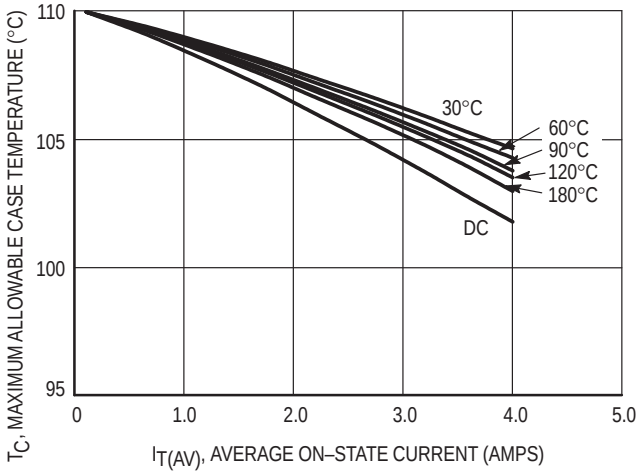


Figure 1. Average Current Derating

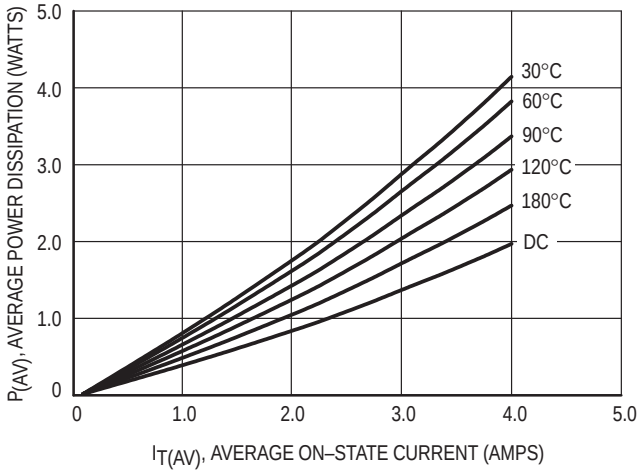


Figure 2. On–State Power Dissipation

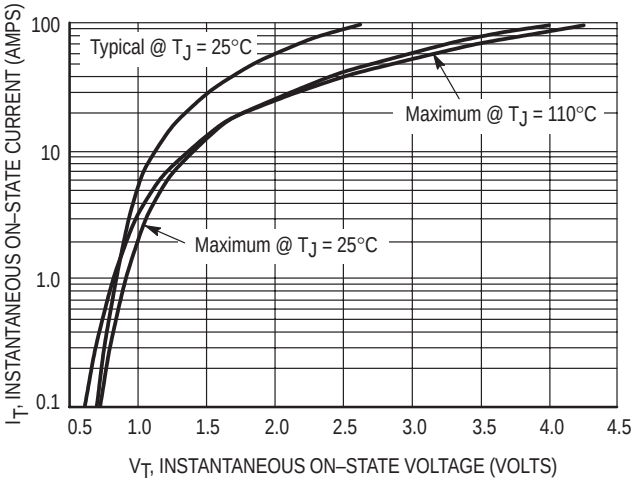


Figure 3. On–State Characteristics

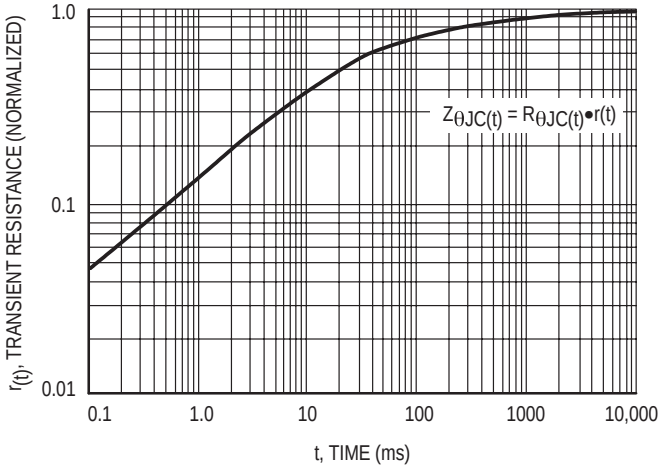


Figure 4. Transient Thermal Response

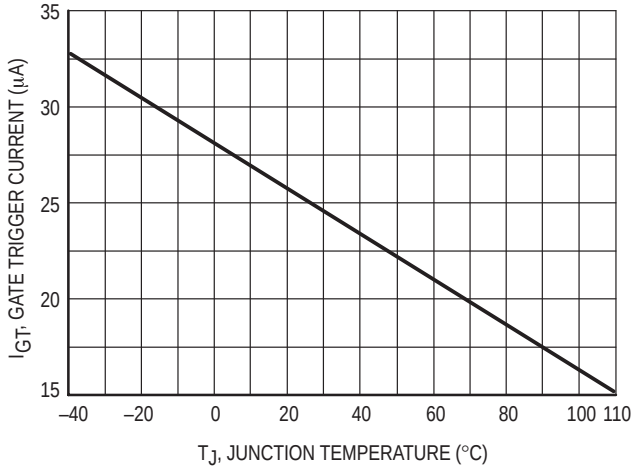


Figure 5. Typical Gate Trigger Current versus Junction Temperature

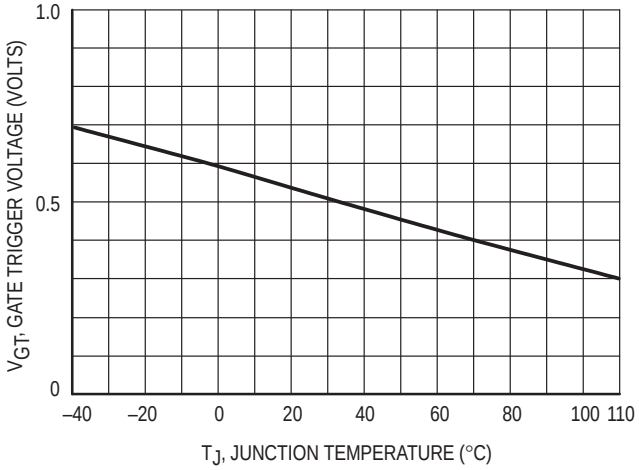


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

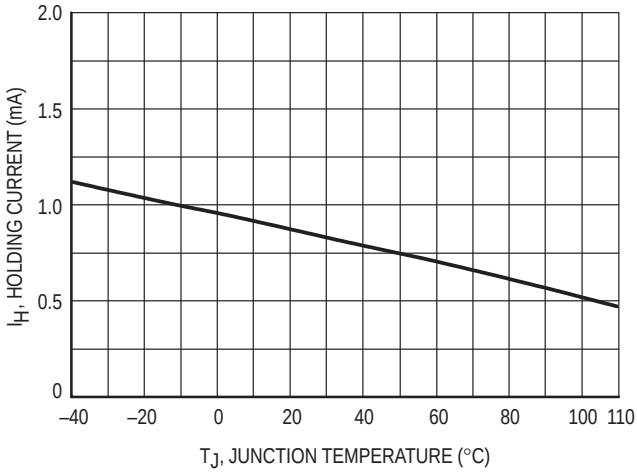


Figure 7. Typical Holding Current versus Junction Temperature

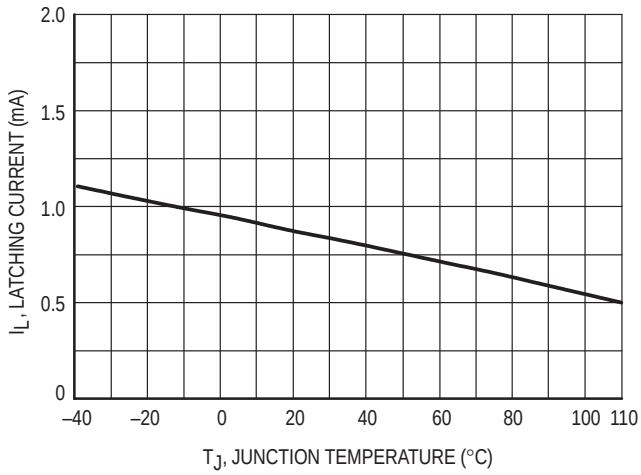
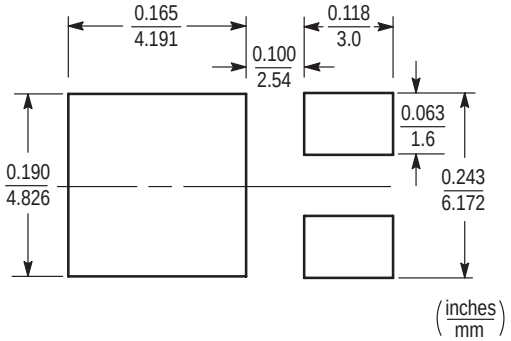


Figure 8. Typical Latching Current versus Junction Temperature

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

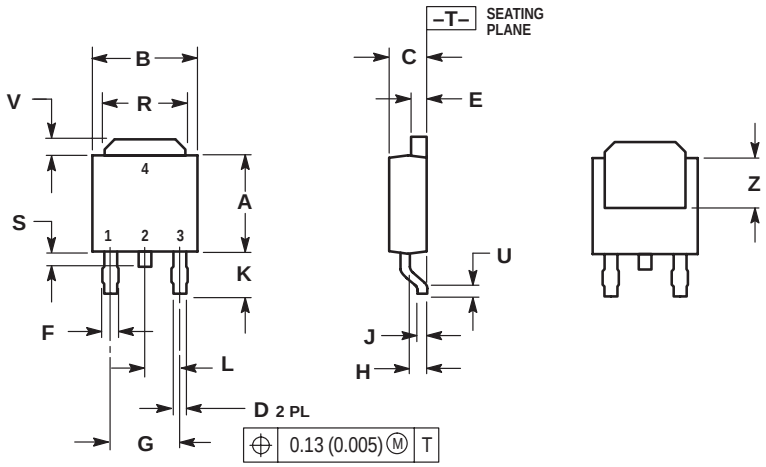
Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



DPAK

PACKAGE DIMENSIONS

D–PAK
CASE 369A–13
ISSUE Z



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	—	0.51	—
V	0.030	0.050	0.77	1.27
Z	0.138	—	3.51	—

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

Notes

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